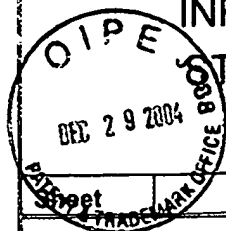


Substitute for Form 1449/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

**Complete if Known**

Application Number	10/750,061
Filing Date	December 30, 2003
First Named Inventor:	Justin K. Brask et al.
Art Unit	2815
Examiner Name	Fenty, Jesse A.
Attorney Docket Number	42P16680

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)				
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
WL		EP	0 623 963 A1	11/9/1994	Siemens AG		
WL		WO	02/43151A	5/30/2002	Hitachi ULSI Sys Co Ltd		

Examiner Signature	<i>W. A. Fenty</i>	Date Considered	3/17/05
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Substitute for Form 1449/PTO			Complete if Known		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>			Application Number	10/750,061	
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			Art Unit	2815	
			Examiner Name	Fenty, Jesse A.	
Sheet	2	of	2	Attorney Docket Number	42P16680
<b>NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T <sup>2</sup>
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*Walter J. Zurek* 3/17/2005